TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

## **HN3C12FU**

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

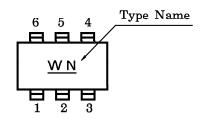
• Including Two Devices in US6 (Ultra Super Mini Type with 6 Leads)

## MAXIMUM RATINGS (Ta = 25°C)

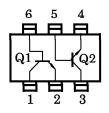
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	20	V
Collector-Emitter Voltage	$v_{CEO}$	10	V
Emitter-Base Voltage	$V_{\mathrm{EBO}}$	1.5	V
Base Current	$I_{\mathrm{B}}$	7	mA
Collector Current	$I_{\mathbf{C}}$	15	mA
Collector Power Dissipation	PC*	200	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	$^{\circ}\mathrm{C}$

\*: Total

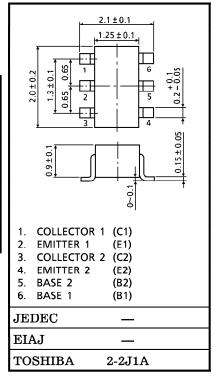
**MARKING** 



PIN ASSIGNMENT (TOP VIEW)



Unit in mm



## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=10V, I_{E}=0$	_	_	1	$\mu$ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=1V, I_{C}=0$	_	_	1	$\mu$ A
DC Current Gain	$\mathbf{h_{FE}}$	$V_{CE}=6V, I_{C}=7mA$	50	_	160	_
Transition Frequency	${ m f_T}$	$V_{CE}=6V, I_{C}=7mA$	7	10	<b> </b>	GHz
Insertion Gain	$ S_{21e} ^2$	$V_{CE}=6V, I_{C}=7mA, f=2GHz$	4	7	_	dB
Noise Figure	NF	$V_{CE}$ =6V, $I_{C}$ =3mA, f=2GHz	_	1.8	3	dB
Reverse Transfer Capacitance Q1	$\mathrm{C_{re}}$	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz (Note)	_	0.4	0.9	pF
Reverse Transfer Capacitance Q2	$C_{\mathbf{re}}$		_	0.35	0.85	pF

(Note) Cre is measured by 3 terminal method capacitance bridge.

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